

Structural and magnetic properties of low-energy Gd implanted ZnO single crystals

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ABSTRACT

We report the structural and magnetic properties of ZnO single crystals implanted with Gd ions at 40 keV. Ion beam analysis shows that after implantation up to 12% of the near-surface atoms are Gd, with most of the Gd ions occupying substitutional lattice sites. The carrier concentration of implanted films is up to several orders of magnitude larger than in unimplanted ZnO. Room temperature ferromagnetism was observed in Gd implanted and annealed ZnO. Zero-field cooled magnetisation curves reveal the presence of super-paramagnetic clusters. The annealing can cause the diffusion and/or migration of implanted ions and intrinsic defects and possibly the formation of super-paramagnetic clusters suggesting that the annealing plays a significant role towards the observed magnetic properties.

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1. Introduction

Electron spin provides an additional degree of freedom that can potentially be exploited in novel semiconductor devices [1]. The combination of electron charge and spin, termed as “spintronics”, can be realized in several materials such as dilute magnetic semiconductors (DMSs), rare-earth nitrides [1–3], etc. The carrier mediated mechanism was proposed to explain the observed phenomenon in DMSs [2]. Zinc oxide (ZnO) doped with transition metal (TM) atoms, up to several atomic%, has been predicted to demonstrate room temperature ferromagnetic ordering [4]. This was followed by several experimental investigations where Curie temperatures of as high as 790 K were reported [5]. However, the observation of room temperature ferromagnetism in the systems with poor conductivity or highly resistive materials suggests that there could also be some other mechanism [5]. The most likely reason could be the inclusion of magnetic ions as secondary phases and/or metallic clusters [6]. Several non magnetic ions (e.g. C) were doped into ZnO to overrule the segregation and precipitation of magnetic ions into the material [7]. The room temperature ferromagnetism has also been observed in pure ZnO, which suggests that the intrinsic defects can also play a significant role towards the observed property [8]. Oxygen vacancies (V_o) and zinc interstitials (Zn_i) are common intrinsic defects present in the ZnO which can occur during sample growth and post growth treatments. Thus,

room temperature ferromagnetism is highly sensitive to the preparation technique and post growth treatments along with the impurity magnetic ions. Recently, high magnetic moment has been observed in GaN [9] and ZnO doped with rare earth (RE) elements [10,11]. RE elements usually have higher magnetic moment compared to TM elements. RE doped ZnO has mainly been investigated in terms of optical properties [12,13]. Recent reports on gadolinium (Gd) doped ZnO suggest that the coupling between Gd ions is ferromagnetic which can be enhanced by electron doping [14]. The aim of this paper is to investigate the structural properties of Gd implanted into ZnO single crystals and subsequent effects on the magnetic property.

2. Experimental procedure

The Zn-face of hydrothermally grown ZnO(0001) was implanted with 40 keV Gd ions using a low energy ion implanter [15–17]. Implanted Gd fluences range from 6.7×10^{14} to $3.0 \times 10^{16} \text{ cm}^{-2}$ resulting in 0.7 to 12 at.% Gd in the near surface region of ZnO, with average implantation depth of 12 nm and maximum depth of 25 nm as was found by theoretical calculation using DYNAMIC-TRIM [18] (see Fig. 1). The implanted samples were subsequently annealed in a vacuum chamber with base pressure $P_b \sim 1 \times 10^{-7} \text{ mbar}$ [17]. Rutherford backscattering spectrometry (RBS) measurements were performed for compositional analysis and depth profiling with a collimated 2 MeV He^+ beam. Rutherford backscattering spectrometry and channeling (RBS/C) analyses were carried out to estimate the crystalline quality upon implantation and annealing. Structural modifications were investigated applying

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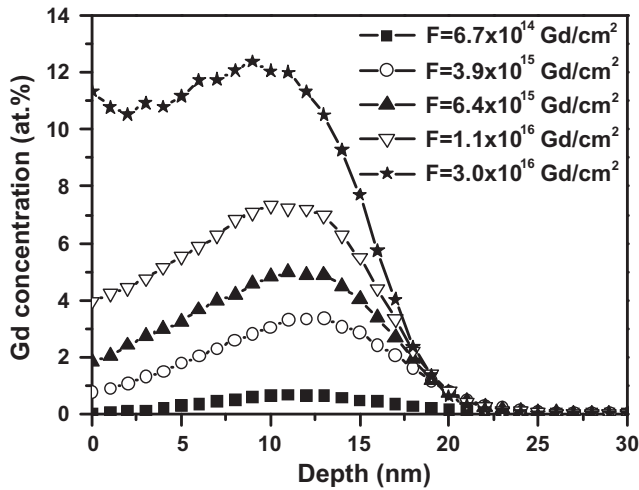


Fig. 1. Gd depth profiles calculated with DYNAMIC-TRIM for Gd implanted at 40 keV into ZnO in the fluence range from 6.7×10^{14} to $3.0 \times 10^{16} \text{ cm}^{-2}$.

Raman spectroscopy using a Jobin–Yvon LabRam micro-Raman system at ambient temperature. An Ar^+ laser with wavelength 514 nm was an excitation source and the spectra were collected in backscattering geometry with a liquid nitrogen-cooled charge coupled device detector. Hall effect measurements were performed at room temperature using the Van der Pauw geometry. A Quantum Design MPMS superconducting quantum interference device (SQUID) was employed to study the magnetic properties of the films.

3. Results and discussion

To characterise the depth profile and lattice location of the implanted Gd ions RBS and RBS/C measurements were carried out on all samples. The retained doses, composition and the thickness information were extracted using the Rutherford Universal Manipulation Program (RUMP) [15]. Fig. 2 shows the RBS spectra of an unimplanted and a sample implanted with $3.9 \times 10^{15} \text{ Gd cm}^{-2}$ and vacuum annealed at 650°C in random and channelled conditions. The RBS spectra demonstrate the near-surface nature of the implantation, consistent with the results shown in Fig. 1. The

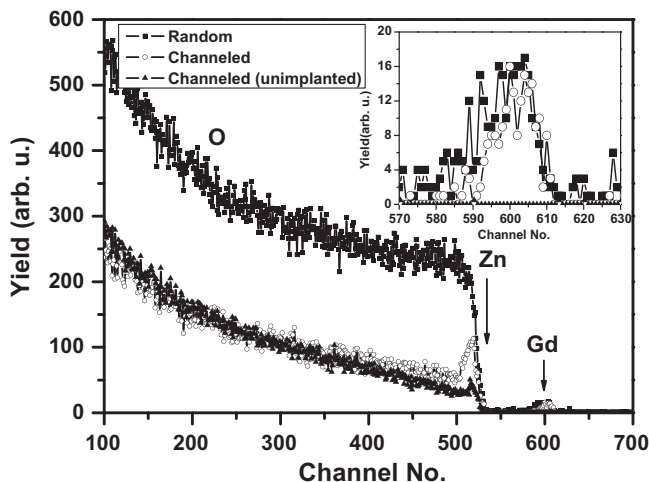


Fig. 2. Random and (0001)-aligned RBS spectra of an unimplanted, $3.9 \times 10^{15} \text{ Gd cm}^{-2}$ implanted and vacuum annealed at 650°C ZnO. The inset shows an expanded view of the Gd peak.

channeled spectrum is considerably attenuated, indicating that this sample retains relatively good crystallinity after implantation.

In Fig. 3(a) and (b) the RBS/C measurements carried out along the $\langle 0001 \rangle$ direction of the ZnO lattice are shown for the sample implanted with $3.9 \times 10^{15} \text{ Gd cm}^{-2}$, both before and after annealing at 650°C . The ratio of the RBS yield in channeling and random, termed as X_{\min} , was collected as a function of the incident beam angle for both Zn and Gd. The $^{\text{Zn}}X_{\min}$ value of around 27% for the unannealed sample is somewhat larger than the value of 7% for unimplanted ZnO, suggesting that the material is partly crystalline and well below the amorphization threshold. After annealing $^{\text{Zn}}X_{\min}$ reduces to 22%. The corresponding values of $^{\text{Gd}}X_{\min}$ are 56% and 64% for as implanted and annealed samples, respectively. The data for Zn and Gd follow similar trends, suggesting that both ions are subjected to similar types of lattice disorder, although the larger $^{\text{Gd}}X_{\min}$ values imply that the Gd ions are more disordered overall. The fraction of Gd ions located on Zn substitutional sites can be estimated from [12,13].

$$\text{Gd}_{\text{Zn}} = \frac{(1 - ^{\text{Gd}}X_{\min})}{(1 - ^{\text{Zn}}X_{\min})}$$

Applying this formula around 60% of the Gd ions in the unannealed sample occupy substitutional lattice sites. After annealing the estimated Gd ions at the substitutional sites reduced to 47%, possibly suggesting the occurrence of some clustering in the annealed samples, consistent with the observations reported by Alves et al. for Er implanted ZnO [12] and Wahl et al. [13]. The latter suggest an annealing temperature of around 1050°C is required for complete recovery of the crystalline damage [13]. However, annealing at such elevated temperatures is likely to enhance clustering and potentially lead to the out-diffusion of the implanted ions.

Further investigation of the effects of implantation and subsequent annealing of the ZnO:Gd films was carried out by Raman spectroscopy. The characteristic Raman modes in ZnO are $A_1 + 2B_1 + E_1 + 2E_2$ [19]. The non-polar E_2 modes have two wavenumbers E_2^{high} and E_2^{low} associated with the motion of the O and Zn sub-lattices, respectively. The modes A_1 and E_1 are polar modes, and can be split into transverse (TO) and longitudinal optical (LO) phonons. The E_2 , A_1 (TO), and E_1 (TO) modes are observed when the incident radiation is perpendicular to the c -axis of the sample, whereas E_2 and A_1 (LO) modes are observed when the incident radiation is parallel to the c -axis [20]. Fig. 4(a) shows the Raman spectra obtained from the samples implanted with fluences between 6.7×10^{14} and $3.0 \times 10^{16} \text{ Gd cm}^{-2}$. The spectra are dominated by the strong O and Zn related peaks observed at 438 cm^{-1} (E_2^{high}) and 100 cm^{-1} (E_2^{low}), which are characteristic of high-quality ZnO. The peak near 331 cm^{-1} arises due to the second-order phonon, $2E_2(\text{M})$, scattering [19]. However, there is a broad feature from 520 cm^{-1} to 600 cm^{-1} which consists of two peaks at 540 cm^{-1} and 575 cm^{-1} . The peak at 575 cm^{-1} can be attributed to the A_1 (LO) mode of ZnO, a mode that is usually observed due to disorder in ZnO [20,21]. Observation of this peak has been attributed to the presence of structural defects such as oxygen vacancies (V_{O}) and zinc interstitials (Zn_i) or their complexes [22]. The peak at 540 cm^{-1} is from two phonon scattering from the LA phonon branch, which is also disorder-induced. Fig. 4(b) displays the Raman spectra collected for unimplanted, $3.9 \times 10^{15} \text{ Gd cm}^{-2}$ as-implanted and $3.9 \times 10^{15} \text{ Gd cm}^{-2}$ vacuum annealed samples. As expected annealing helps to recover the implantation induced disorder, similar to the observations of Schumm et al. for air annealed ZnO:Mn [21]. The fact that this is possible after vacuum annealing, which might induce some oxygen loss, implies that the observation of the 540 cm^{-1} and 575 cm^{-1} peaks is not closely related to the

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